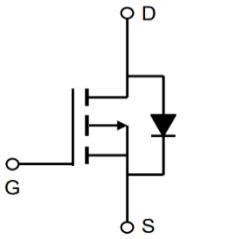
AP40P10P/T

-100V P-Channel Enhancement Mode MOSFET

Description

The AP40P10P/T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = -100V I_D =-40A

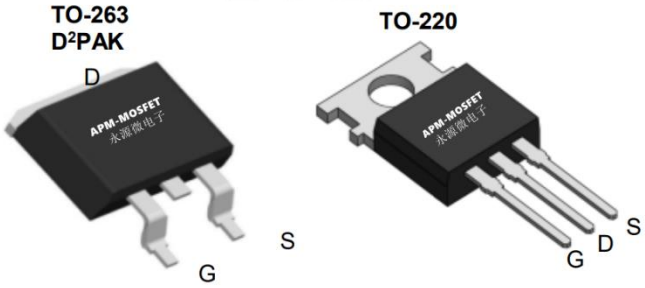
$R_{DS(ON)}$ <55mΩ @ V_{GS}=10V **(Type：48mΩ)**

Application

Brushless motor

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP40P10P	TO-220-3L	AP40P10P XXX YYYY	1000
AP40P10T	TO-263-3L	AP40P10T XXX YYYY	800

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-100	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-29	A
IDM	Pulsed Drain Current[2]	-120	A
EAS	Single Pulse Avalanche Energy[3]	560	mJ
IAS	Avalanche Current	-29	A
P_D@T_C=25℃	Total Power Dissipation[4]	104	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
RθJA	Thermal Resistance Junction-Ambient [1]	62.5	℃/W
RθJC	Thermal Resistance Junction-Case[1]	1.22	℃/W

P-Channel Electrical Characteristics (TJ =25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	-110	---	V
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-10A	---	48	55	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	51	58	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.8	-2.5	V
IDSS	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-10A	---	32	---	S
Q_g	Total Gate Charge	V_{DS}=-80V V_{GS}=-10V I_D=-14A	---	92	---	nC
Qgs	Gate-Source Charge		---	17.5	---	
Qgd	Gate-Drain Charge		---	14	---	
Td(on)	Turn-On Delay Time	V_{DD}=-50V , V_{GS}=-10V ,R_G=3.3Ω, I_D=-14A	---	20.5	---	ns
T_r	Rise Time		---	32.2	---	
Td(off)	Turn-Off Delay Time		---	123	---	
T_f	Fall Time		---	63.7	---	
Ciss	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , f=1MHz	---	6516	---	pF
Coss	Output Capacitance		---	223	---	
Crss	Reverse Transfer Capacitance		---	125	---	
IS	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-40	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V
trr	Reverse Recovery Time	IF=-14A , di/dt=-100A/μs , T_J=25℃	---	31.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	31.97	---	nC

Note :
1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3、The EAS data shows Max. rating . The test condition is V DD =-25V,V GS =-10V,L=0.1mH,IAS =-29A
4、The power dissipation is limited by 150℃ junction temperature
5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

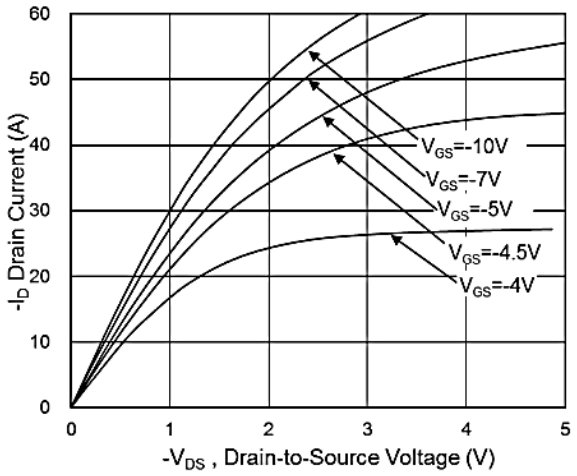


Fig.1 Typical Output Characteristics

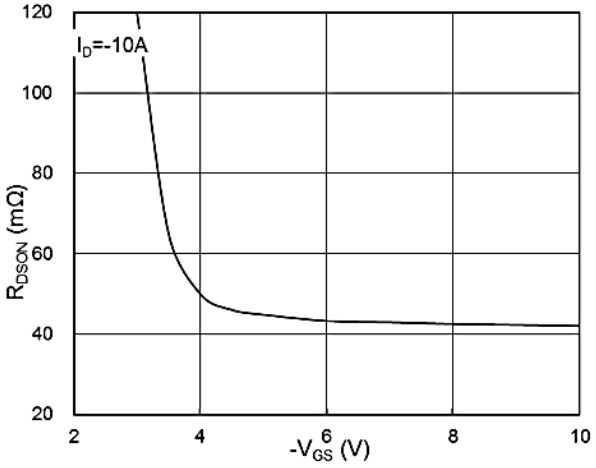


Fig.2 On-Resistance vs G-S Voltage

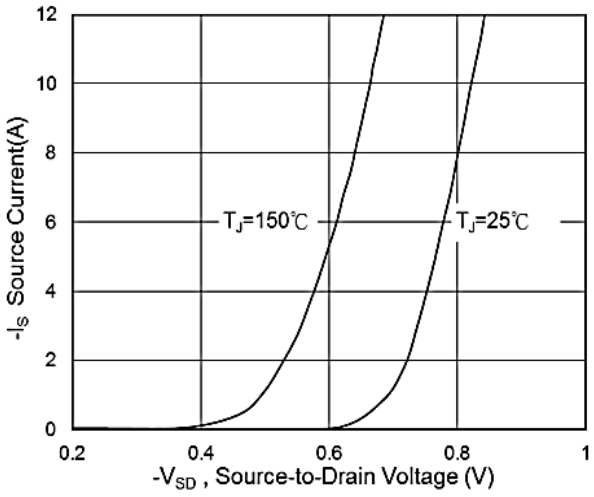


Fig.3 Typical S-D Diode Forward Voltage

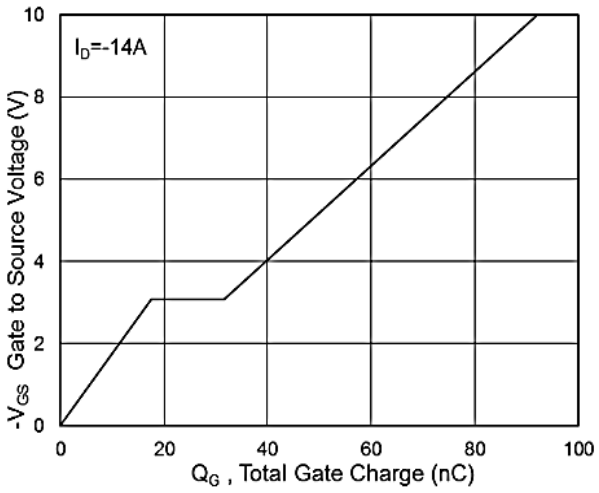


Fig.4 Gate-Charge Characteristics

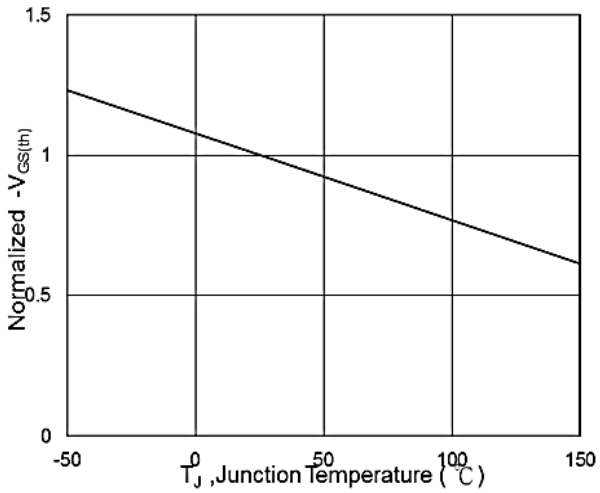


Fig.5 Normalized $V_{GS(th)}$ vs T_J

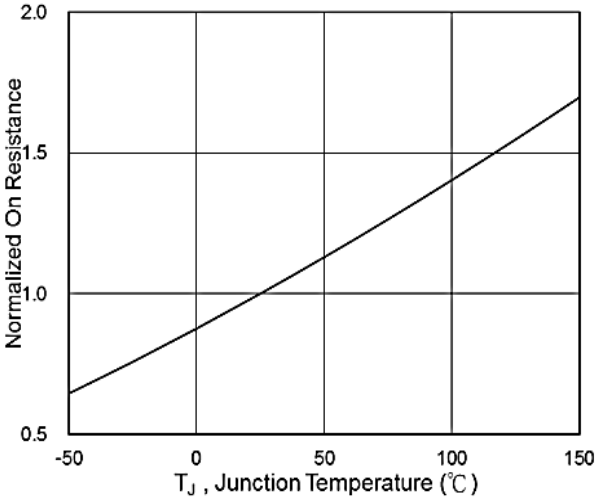


Fig.6 Normalized R_{DSON} vs T_J

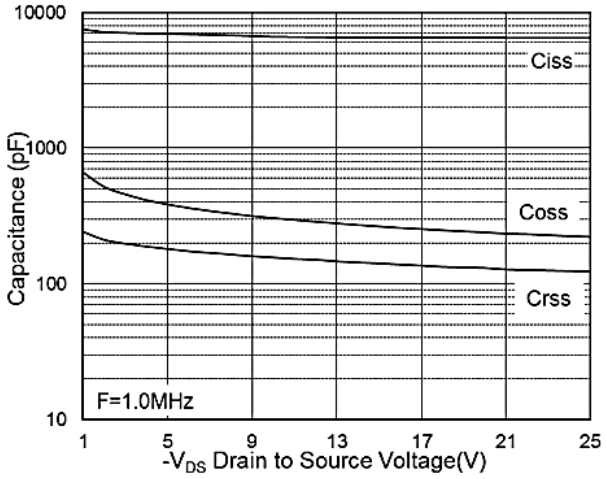


Fig.7 Capacitance

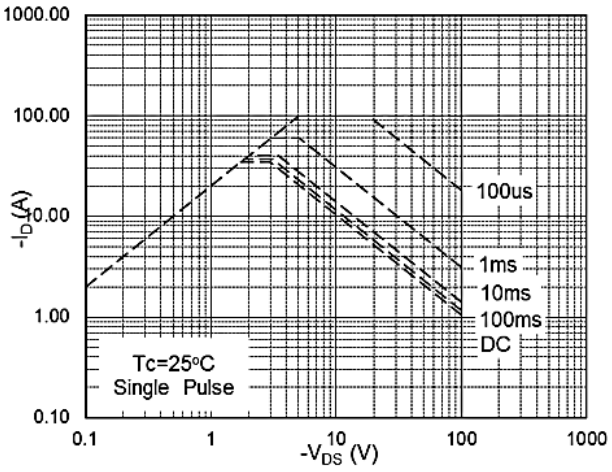


Fig.8 Safe Operating Area

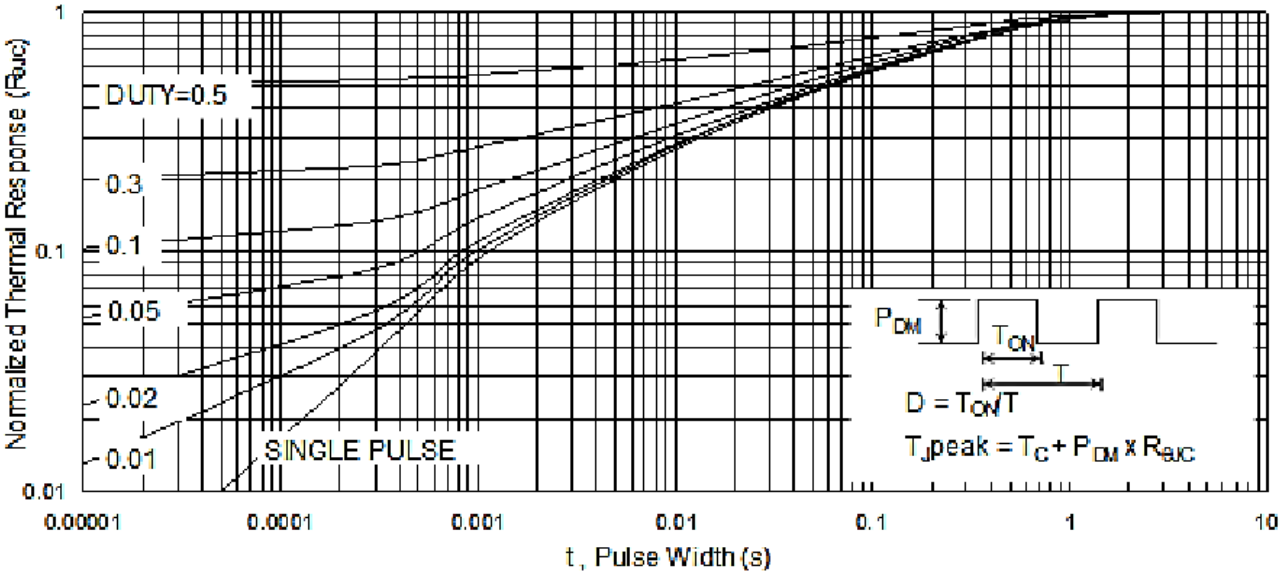


Fig.9 Normalized Maximum Transient Thermal Impedance

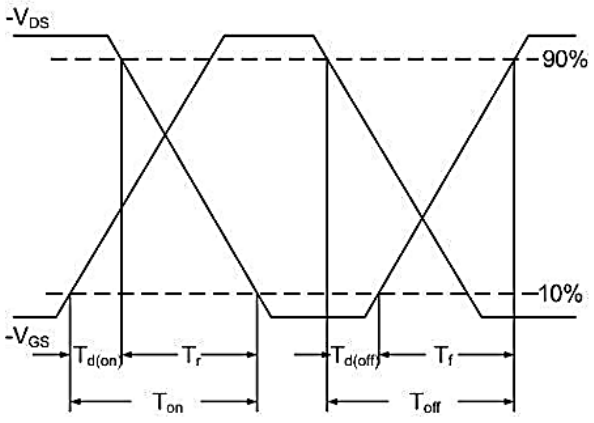


Fig.10 Switching Time Waveform

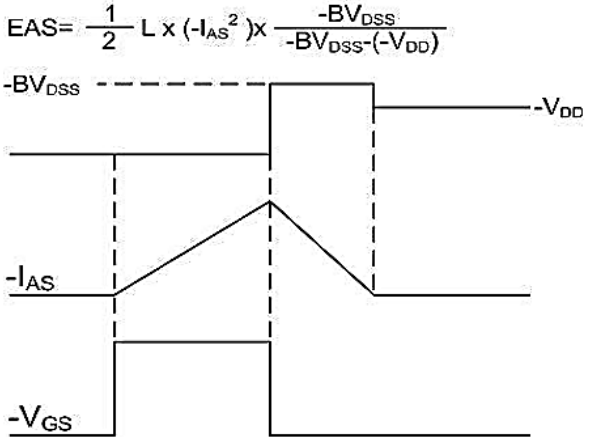
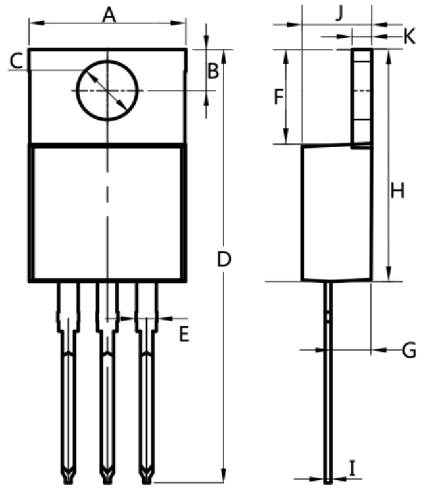


Fig.11 Unclamped Inductive Waveform

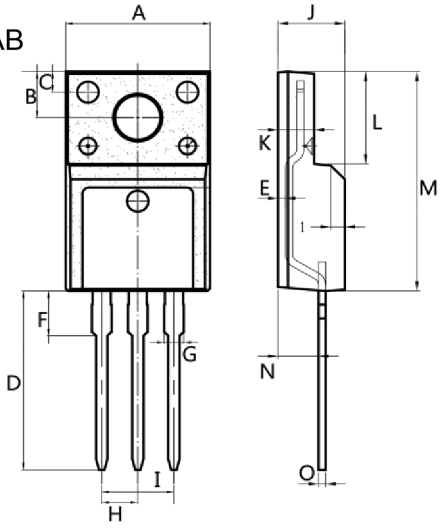
-100V P-Channel Enhancement Mode MOSFET

TO-220AB



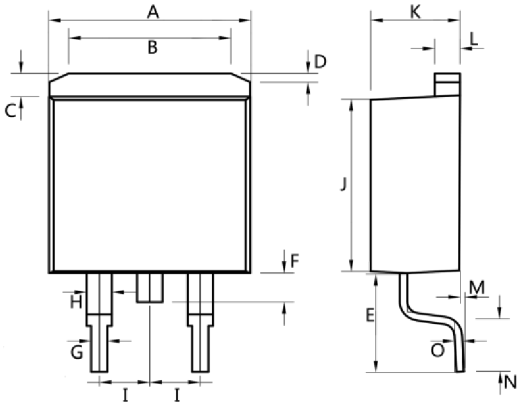
Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4
All Dimensions in millimeter		

ITO-220AB



Dim.	Min.	Max.
A	9.9	10.3
B	2.9	3.5
C	1.15	1.45
D	12.75	13.25
E	0.55	0.75
F	3.1	3.5
G	1.25	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.55	4.75
K	2.4	2. 7
L	6.35	6.75
M	15.0	16.0
N	2.75	3.15
O	0.45	0.60
All Dimensions in millimeter		

TO-263



Dim.	Min.	Max.
A	10.0	10. 5
B	7.25	7.75
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.75	0.95
H	1.15	1.35
I	Typ 2.54	
J	8.4	8.6
K	4.4	4.6
L	1.25	1.45
M	0.02	0.1
N	2.4	2.8
O	0.35	0.45
All Dimensions in millimeter		

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Edition	Date	Change
REV1.0	2023/4/13	Initial release